

DATA SHEET

BT151 series C Thyristors

Product specification

April 2004



Thyristors

BT151 series C

GENERAL DESCRIPTION

Passivated thyristors in a plastic envelope, intended for use in applications requiring high bidirectional blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

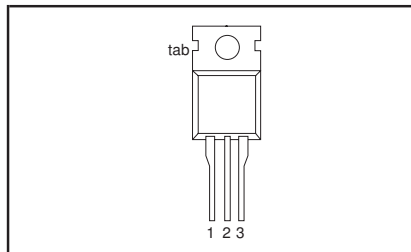
QUICK REFERENCE DATA

| SYMBOL | PARAMETER | MAX. | MAX. | MAX. | UNIT |
|--------------------------|--------------------------------------|-------------|-------------|-------------|------|
| V_{DRM} , V_{RRM} | Repetitive peak off-state voltages | 500C 500 | 650C 650 | 800C 800 | V |
| $I_{T(AV)}$ | Average on-state current | 7.5 | 7.5 | 7.5 | A |
| $I_{T(RMS)}$ | RMS on-state current | 12 | 12 | 12 | A |
| I_{TSM} | Non-repetitive peak on-state current | 100 | 100 | 100 | A |

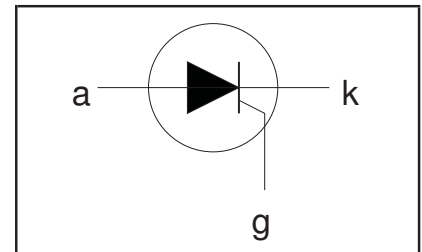
PINNING - TO220AB

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | cathode |
| 2 | anode |
| 3 | gate |
| tab | anode |

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 60134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | | | UNIT |
|--------------------------|--|---|------|---------------------------|---------------------------|--------------|------------------|
| | | | | -500C 500 ¹ | -650C 650 ¹ | -800C 800 | |
| V_{DRM} , V_{RRM} | Repetitive peak off-state voltages | | - | -500C 500 ¹ | -650C 650 ¹ | -800C 800 | V |
| $I_{T(AV)}$ | Average on-state current | half sine wave; $T_{mb} \leq 109\text{ °C}$ | - | 7.5 | | | A |
| $I_{T(RMS)}$ | RMS on-state current | all conduction angles | - | 12 | | | A |
| I_{TSM} | Non-repetitive peak on-state current | half sine wave; $T_j = 25\text{ °C}$ prior to surge | - | 100 | | | A |
| | | $t = 10\text{ ms}$ | - | 110 | | | A |
| | | $t = 8.3\text{ ms}$ | - | 50 | | | A ² s |
| I^2t | I^2t for fusing | $t = 10\text{ ms}$ | - | 50 | | | A/μs |
| di_T/dt | Repetitive rate of rise of on-state current after triggering | $I_{TM} = 20\text{ A}$; $I_G = 50\text{ mA}$; $di_G/dt = 50\text{ mA}/\mu\text{s}$ | - | 50 | | | A/μs |
| I_{GM} | Peak gate current | | - | 2 | | | A |
| V_{GM} | Peak gate voltage | | - | 5 | | | V |
| V_{RGM} | Peak reverse gate voltage | | - | 5 | | | V |
| P_{GM} | Peak gate power | | - | 5 | | | W |
| $P_{G(AV)}$ | Average gate power | over any 20 ms period | - | 0.5 | | | W |
| T_{stg} | Storage temperature | | -40 | 150 | | | °C |
| T_j | Operating junction temperature | | - | 125 | | | °C |

¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the thyristor may switch to the on-state. The rate of rise of current should not exceed 15 A/μs.

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THERMAL RESISTANCES

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|----------------|--|-------------|------|------|------|------|
| $R_{th\ j-mb}$ | Thermal resistance junction to mounting base | in free air | - | - | 1.3 | K/W |
| $R_{th\ j-a}$ | Thermal resistance junction to ambient | | - | 60 | - | K/W |

STATIC CHARACTERISTICS $T_j = 25\text{ °C}$ unless otherwise stated

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|------------|---------------------------|--|------|------|------|------|
| I_{GT} | Gate trigger current | $V_D = 12\text{ V}; I_T = 0.1\text{ A}$ | - | 2 | 15 | mA |
| I_L | Latching current | $V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$ | - | 10 | 40 | mA |
| I_H | Holding current | $V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$ | - | 7 | 20 | mA |
| V_T | On-state voltage | $I_T = 23\text{ A}$ | - | 1.44 | 1.75 | V |
| V_{GT} | Gate trigger voltage | $V_D = 12\text{ V}; I_T = 0.1\text{ A}$ | - | 0.6 | 1.5 | V |
| I_D, I_R | Off-state leakage current | $V_D = V_{DRM(max)}; I_T = 0.1\text{ A}; T_j = 125\text{ °C}$ $V_D = V_{DRM(max)}; V_R = V_{RRM(max)}; T_j = 125\text{ °C}$ | 0.25 | 0.4 | - | V |
| | | | - | 0.1 | 0.5 | mA |

DYNAMIC CHARACTERISTICS $T_j = 25\text{ °C}$ unless otherwise stated

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|-----------|--|--|------|------|------|------------|
| dV_D/dt | Critical rate of rise of off-state voltage | $V_{DM} = 67\% V_{DRM(max)}; T_j = 125\text{ °C};$ exponential waveform; | | | | |
| | | Gate open circuit $R_{GK} = 100\ \Omega$ | 50 | 130 | - | V/ μ s |
| t_{gt} | Gate controlled turn-on time | $I_{TM} = 40\text{ A}; V_D = V_{DRM(max)}; I_G = 0.1\text{ A};$ $dI_G/dt = 5\text{ A}/\mu\text{s}$ | 200 | 1000 | - | V/ μ s |
| t_q | Circuit commutated turn-off time | $V_D = 67\% V_{DRM(max)}; T_j = 125\text{ °C};$ $I_{TM} = 20\text{ A}; V_R = 25\text{ V}; dI_{TM}/dt = 30\text{ A}/\mu\text{s};$ $dV_D/dt = 50\text{ V}/\mu\text{s}; R_{GK} = 100\ \Omega$ | - | 70 | - | μ s |

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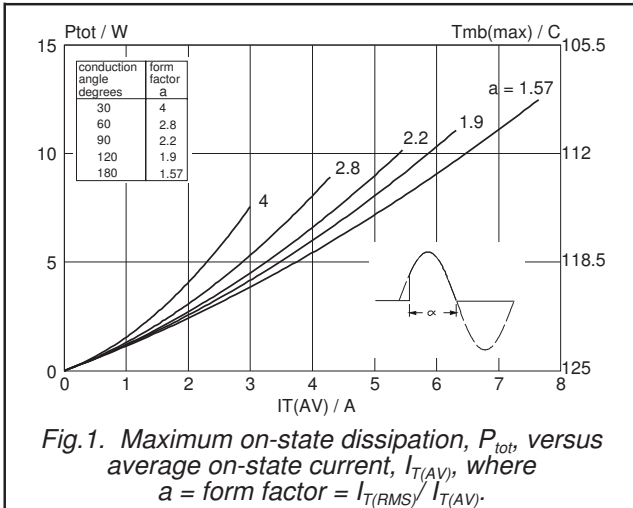


Fig. 1. Maximum on-state dissipation, P_{tot} , versus average on-state current, $I_{T(AV)}$, where $a = \text{form factor} = I_{T(RMS)} / I_{T(AV)}$.

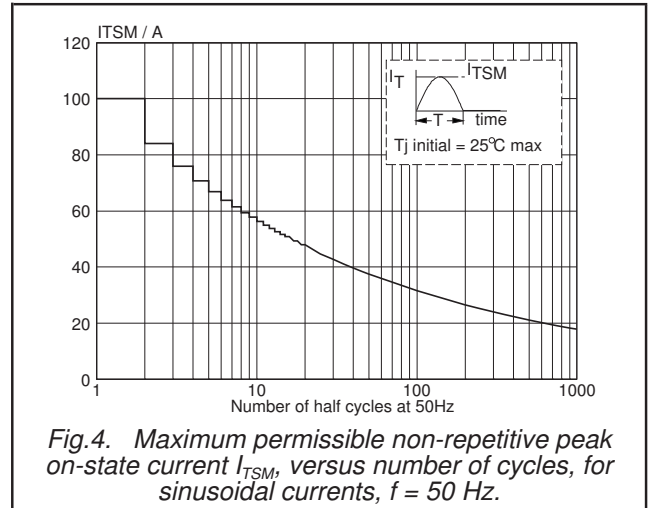


Fig. 4. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus number of cycles, for sinusoidal currents, $f = 50 \text{ Hz}$.

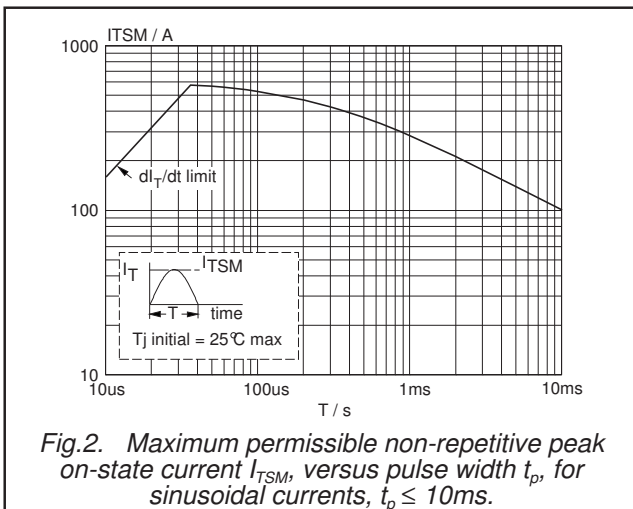


Fig. 2. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \leq 10 \text{ ms}$.

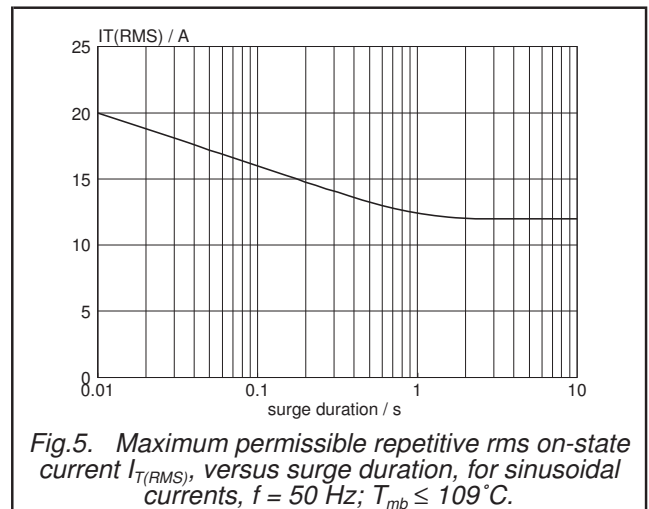


Fig. 5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, $f = 50 \text{ Hz}$; $T_{mb} \leq 109^\circ \text{C}$.

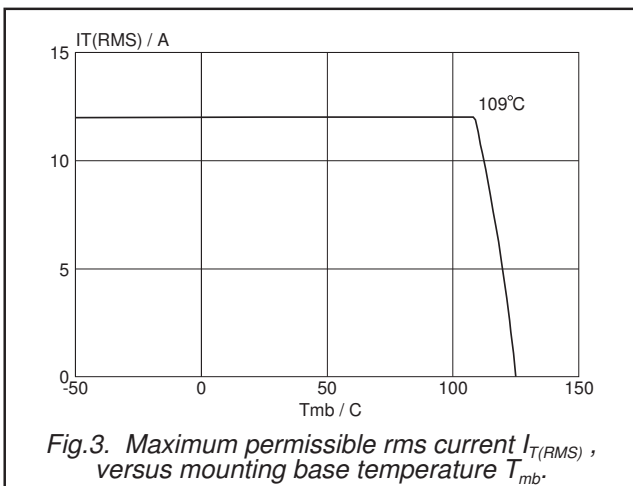


Fig. 3. Maximum permissible rms current $I_{T(RMS)}$, versus mounting base temperature T_{mb} .

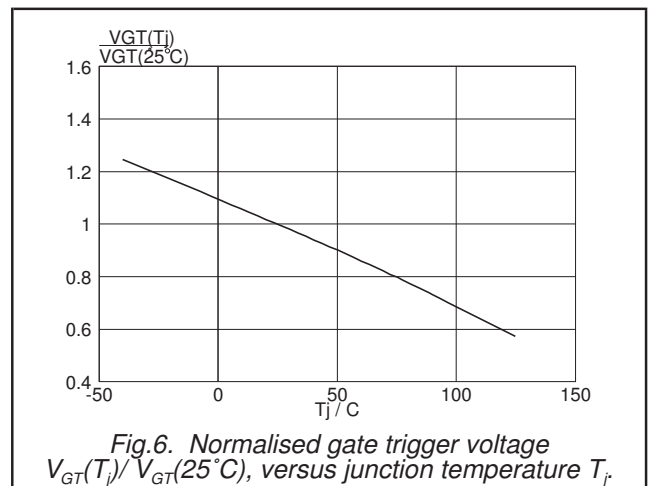
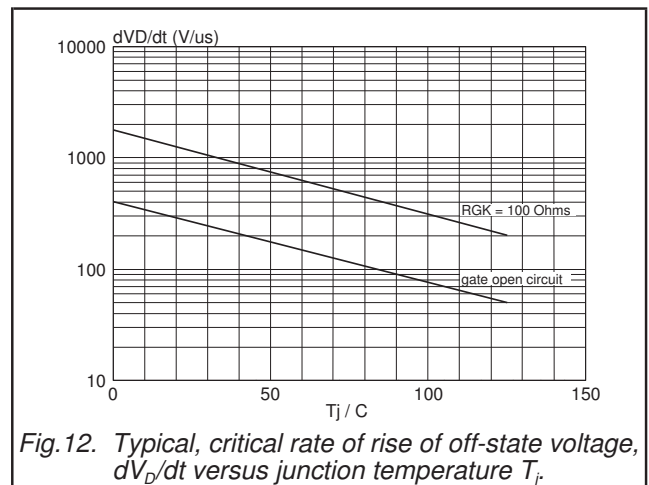
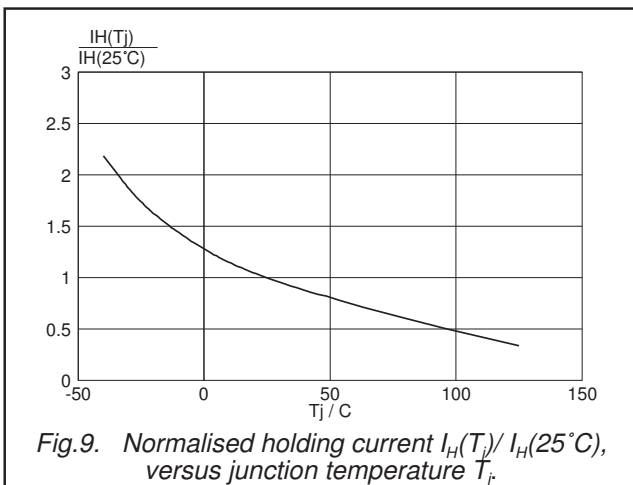
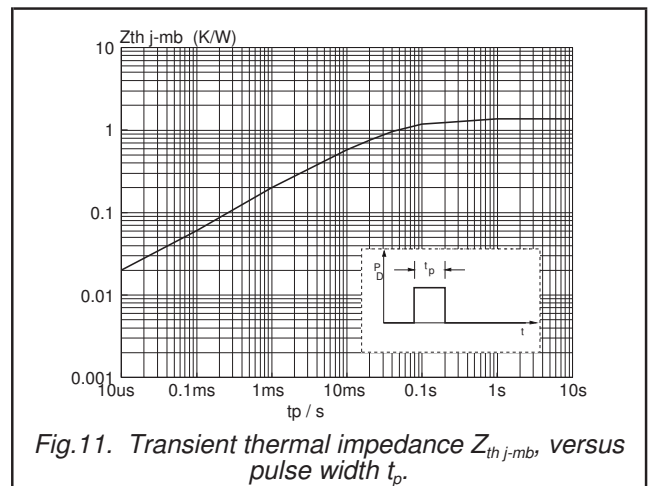
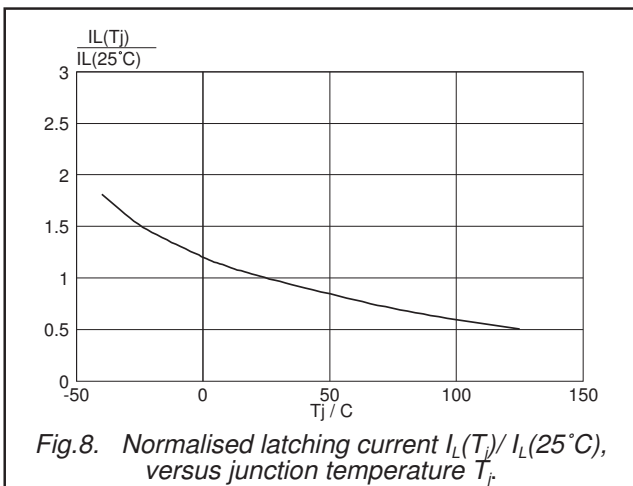
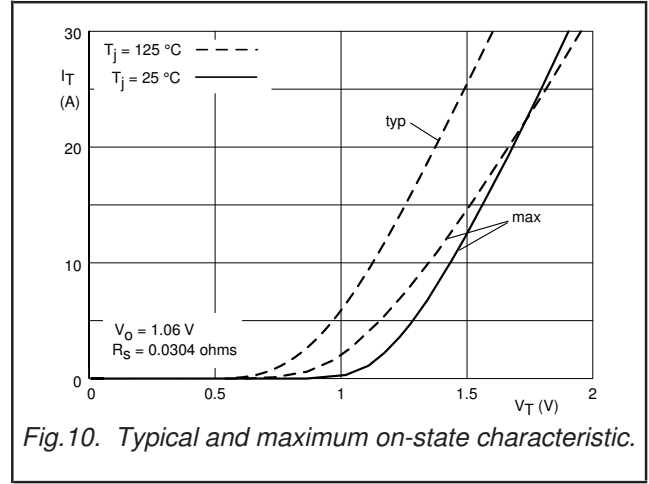
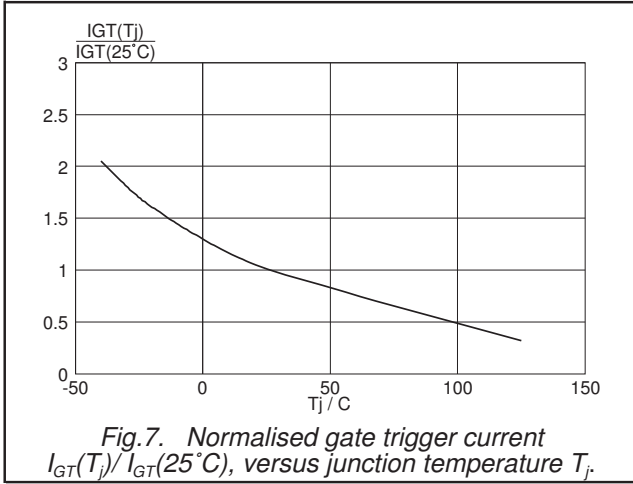


Fig. 6. Normalised gate trigger voltage $V_{GT}(T_j) / V_{GT}(25^\circ \text{C})$, versus junction temperature T_j .

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MECHANICAL DATA

Dimensions in mm

Net Mass: 2 g

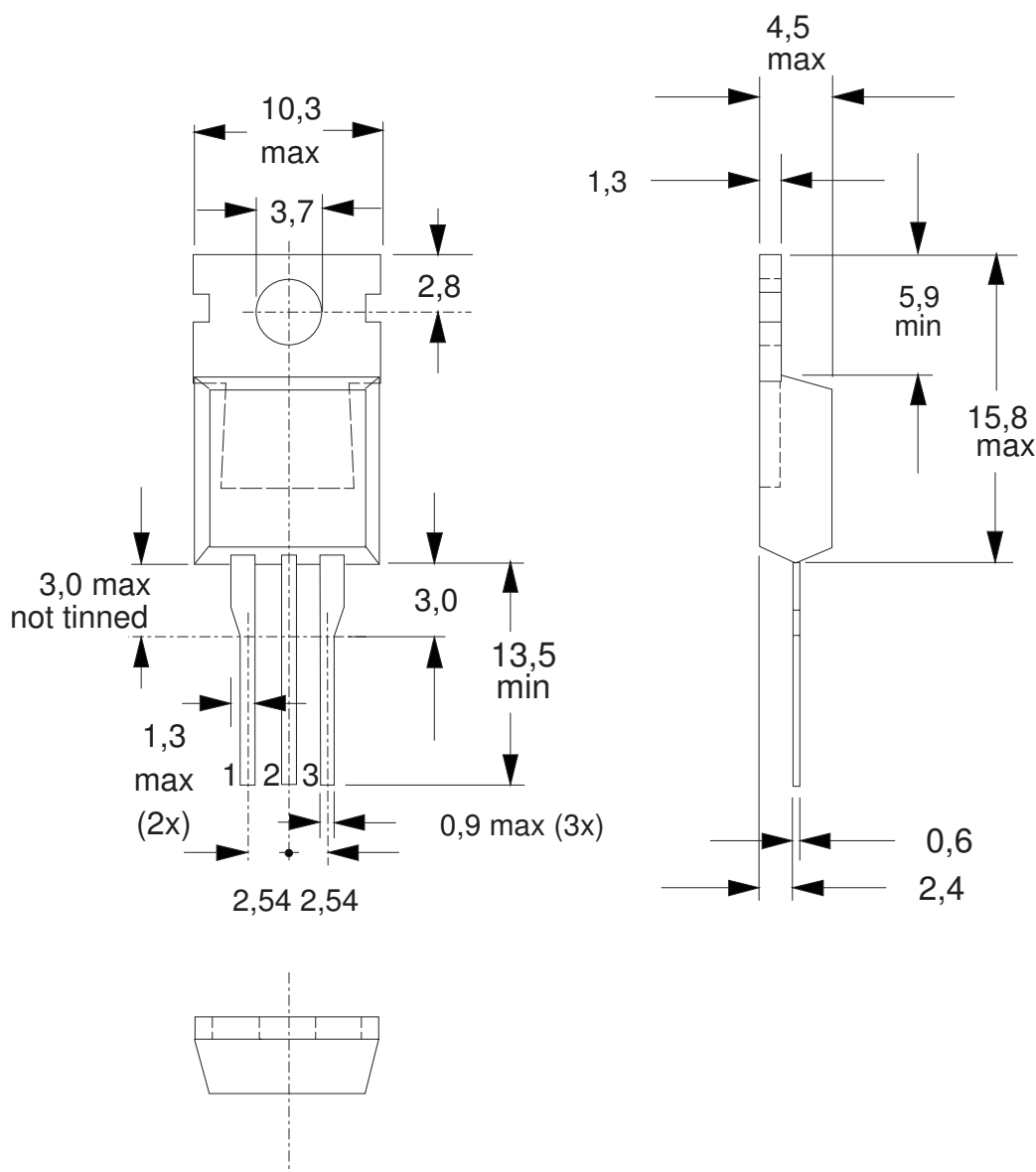


Fig.13. SOT78 (TO220AB). pin 2 connected to mounting base.

Notes

1. Refer to mounting instructions for SOT78 (TO220) envelopes.
2. Epoxy meets UL94 V0 at 1/8".

Legal information

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| DOCUMENT STATUS ⁽¹⁾ | PRODUCT STATUS ⁽²⁾ | DEFINITION |
|--------------------------------|-------------------------------|---|
| Objective data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary data sheet | Qualification | This document contains data from the preliminary specification. |
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